

isc Silicon NPN Power Transistor

2SD214

DESCRIPTION

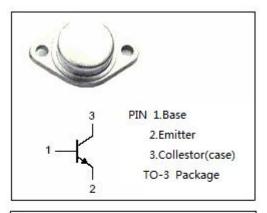
- Excellent Safe Operating Area
- Collector-Emitter Sustaining Voltage-
- : V_{CEO(SUS)}= 100V(Min.)
- Low Collector Saturation Voltage-
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

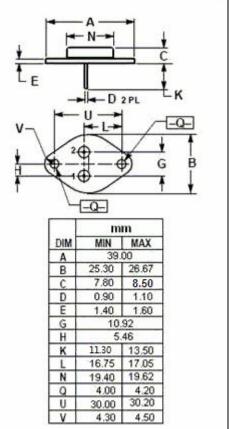
APPLICATIONS

Designed for high power amplifier and switching applications

| SYMBOL | PARAMETER | МАХ | UNIT | |
|------------------|--|---------|------|--|
| V _{CBO} | Collector-Base Voltage | 130 | V | |
| V _{CEO} | Collector-Emitter Voltage | 100 | V | |
| Vebo | Emitter-Base Voltage | 6 | V | |
| lc | Collector Current-Continuous | 10 | A | |
| I _{CP} | Collector Current-Peak | 20 | A | |
| Pc | $\begin{array}{c} \mbox{Collector Power Dissipation} \\ \mbox{@}T_{C}\mbox{=}25^{\circ}\!\!\mathbb{C} \end{array} \end{array} \end{tabular} 100$ | | W | |
| Tj | Junction Temperature | 150 | °C | |
| T _{stg} | Storage Temperature Range | -65~150 | ĉ | |

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)







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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|-----------------------|--------------------------------------|---|-----|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | I _C = 10mA ; I _B = 0 | 100 | | V |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = 5A; I _B = 0.5A | | 1.5 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 5Α; I _B = 0.5Α | | 2.0 | V |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 100V; I _B = 0 | | 1.0 | mA |
| І _{сво} | Collector Cutoff Current | V _{CB} = 130V; I _E = 0 | | 0.1 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5.0V; I _C = 0 | | 0.1 | mA |
| h _{FE-1} | DC Current Gain | I _C = 1A ; V _{CE} = 4V | 60 | 200 | |
| h _{FE-2} | DC Current Gain | I _C = 5A ; V _{CE} = 4V | 30 | | |
| f⊤ | Current Gain-Bandwidth Product | I _C = 0.5A ; V _{CE} = 10V;f= 1.0MHz | 8.0 | | MHz |

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